Amendments to the Claims:

Please amend the claims as follows:

Claim 1 (Currently Amended) A semiconductor device comprising:

a substrate;

a plurality of protruding ~~portion~~ portions which ~~is~~ are formed on the top face of the substrate; and

a conductive layer wiring which is formed on the substrate so as to have a spiral shape and which serve as an induction element,

wherein all of said protruding ~~portion~~ portions ~~is~~ are formed only in a region other than a region directly below said conductive layer wiring.

Claim 2 (Currently Amended) A semiconductor device as set forth in claim 1, wherein the substrate is an SOI substrate, and

said protruding ~~portion~~ portions ~~is~~ are formed of an SOI layer of said SOI substrate.

Claim 3 (Previously Presented): A semiconductor device as set forth in claim 2, wherein the substrate includes an N-type semiconductor layer.

Claim 4 (Previously Presented): A semiconductor device as set forth in claim 2, wherein the substrate includes a P-type semiconductor layer.

Claim 5 (Previously Presented): A semiconductor device comprising:

a substrate which has an inductor region;

a protruding portion which is formed on the top face of the substrate;

a conductive layer wiring which is formed in said inductor region on the substrate so as to have a spiral shape and which serves as an induction element; and

a protective film which is formed in said inductor region between the substrate and said conductive layer and prevents silicidation of said protruding portion in said inductor region.

Claim 6 (Previously Presented): A semiconductor device as set forth in claim 5, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 7 (Previously Presented): A semiconductor device as set forth in claim 6, which further comprises an extracting wiring which is connected to said conductive layer wiring.

Claim 8 (Previously Presented): A semiconductor device as set forth in claim 6, wherein the substrate includes an N-type semiconductor layer.

Claim 9 (Previously Presented): A semiconductor device as set forth in claim 6, wherein the substrate includes a P-type semiconductor layer.

Claim 10 (Previously Presented): A semiconductor device as set forth in claim 5, wherein said protruding portion is formed exclusively in a region other than a region directly below said conductive layer wiring.

Claim 11 (Previously Presented): A semiconductor device as set forth in claim 10, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 12 (Previously Presented): A semiconductor device as set forth in claim 11, which further comprises an extracting wiring which is connected to said conductive layer wiring.

Claim 13 (Previously Presented): A semiconductor device as set forth in claim 11, wherein the substrate includes an N-type semiconductor layer.

Claim 14 (Previously Presented): A semiconductor device as set forth in claim 11, wherein the substrate includes a P-type semiconductor layer.

Claims 15 (Withdrawn): A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate and which includes a spiral conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed in a region other than the region in which said conductive layer is formed, the top of said protruding portion serving as a dummy element for controlling a chemical mechanical polishing process.

Claim 16 (Withdrawn): A method for fabricating a semiconductor integrated circuit device as set forth in claim as set forth in claim 15, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 17 (Withdrawn): A method for fabricating a semiconductor integrated circuit device comprising a substrate, and a spiral inductor which is formed on the substrate so as to have a spiral shape and which includes a conductive layer serving as an induction element, said method comprising:

forming an element isolating groove in the surface of the substrate so that a protruding portion is formed, the top thereof serving as a dummy element for controlling a chemical mechanical polishing process;

depositing a protective film on the substrate;

selectively removing said protective film in a region other than a region in which said induction element is to be formed, by patterning using a photoresist; and

silicidating the surface of the substrate.

Claim 18 (Withdrawn): A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 19 (Withdrawn): A method for fabricating a semiconductor integrated circuit device as set forth in claim 17, wherein said protruding portion is formed in a region other than a region directly below said conductive layer.

Claim 20 (Withdrawn): A method for fabricating a semiconductor integrated circuit device as set forth in claim as set forth in claim 19, wherein the substrate is an SOI substrate, and

said protruding portion is formed of an SOI layer of said SOI substrate.

Claim 21 (Currently Amended) A semiconductor device comprising:

a substrate;

a plurality of protruding ~~portion~~ portions which ~~is~~ are formed on the top face of the substrate and ~~the~~ each top of which serves as a dummy element for controlling a chemical mechanical polishing process; and

a conductive layer wiring which is formed on the substrate so as to have a spiral shape and which serves as an induction element,

wherein all of said protruding ~~portion~~ portions ~~is~~ are formed only in a region other than a region directly below said conductive layer wiring.

Claim 22 (Previously Presented): A semiconductor device comprising:

a substrate which has an inductor region;

a protruding portion which is formed on the top face of the substrate;

a conductive layer wiring which is formed in said inductor region on the substrate so as to have a spiral shape and which serves as an induction element; and

a protective film which is formed only in said inductor region between the substrate and said conductive layer and prevents silicidation of said protruding portion in said inductor region.

Claim 23 (Previously Presented): A semiconductor device comprising:

a substrate which has a first region for an induction element and a second region for an active element;

a protruding portion which is formed on the top face of the substrate;

a conductive layer wiring which is formed in said first region on the substrate so as to have a spiral shape and which serves as an induction element; and

a protective film which is formed in said first region between the substrate and said conductive layer and prevents silicidation of said protruding portion in said first region during silicidation of the active element in said second region.